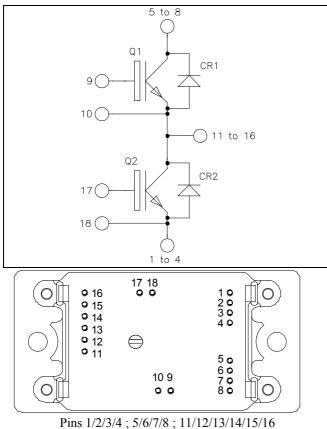


Phase leg Fast Trench + Field Stop IGBT3 Power Module



must be shorted together

APTGT150A1202G

$V_{CES} = 1200V$ $I_{C} = 150A$ @ Tc = 80°C

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Fast Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHzSoft recovery parallel diodes
 - Soft recovery paralle
 Low diode VF
 - Low cloue v1
 Low leakage current
 - RBSOA and SCSOA rated
 - Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant

All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage		1200	V
I _C	Continuous Collector Current	$T_C = 25^{\circ}C$	220	
	Continuous Conector Current	$T_C = 80^{\circ}C$	150	А
I _{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	350	
V _{GE}	Gate – Emitter Voltage		±20	V
PD	Maximum Power Dissipation	$T_C = 25^{\circ}C$	690	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	300A @ 1150V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				50	μA
V _{CE(sat)}	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.7	2.1	V
		$I_{\rm C} = 150 {\rm A}$ $T_{\rm j} =$	$T_{j} = 125^{\circ}C$		2.0		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 3 \text{ mA}$		5.0	5.8	6.5	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$		10.7		
Coes	Output Capacitance	$V_{CE} = 25V$		0.56		nF
C _{res}	Reverse Transfer Capacitance	f = 1 MHz		0.48		
Q _G	Gate charge	V _{GE} =±15V, I _C =150A V _{CE} =600V		1.4		μC
T _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C)		280		
Tr	Rise Time	$V_{GE} = \pm 15 V$		40		
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 150A$		420		ns
$T_{\rm f}$	Fall Time	$R_G = 2.2\Omega$		75		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (125°C)		290		
Tr	Rise Time	$V_{GE} = \pm 15V$		45		
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 150A$		520		ns
$T_{\rm f}$	Fall Time	$R_G = 2.2\Omega$		90		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $T_j = 125^{\circ}C$		14		mJ
$\mathrm{E}_{\mathrm{off}}$	Turn-off Switching Energy	$I_{\rm C} = 150 {\rm A}$ $R_{\rm G} = 2.2 {\Omega}$ $T_{\rm j} = 125^{\circ} {\rm C}$		16		1115
I _{sc}	Short Circuit data	$V_{GE} \le 15V$; $V_{Bus} = 900V$ $t_p \le 10\mu s$; $T_j = 125^{\circ}C$		600		А
R _{thJC}	Junction to Case Thermal Resistance				0.18	°C/W

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I _{RM}	Maximum Reverse Leakage Current	V _R =1200V				50	μΑ
$I_{\rm F}$	DC Forward Current		$Tc = 80^{\circ}C$		150		А
$V_{\rm F}$	Diode Forward Voltage	$I_{\rm F} = 150 {\rm A}$	$T_j = 25^{\circ}C$		1.6	2.1	v
			$T_i = 125^{\circ}C$		1.6		
t _{rr}	Reverse Recovery Time		$T_j = 25^{\circ}C$		170		ns
٩r		I = 150 A	$T_{j} = 125^{\circ}C$		280		110
0	Reverse Recovery Charge	$I_{\rm F} = 150 \text{A}$ $V_{\rm R} = 600 \text{V}$	$T_j = 25^{\circ}C$		15		μC
Q _{rr}	Reverse Recovery Charge	$di/dt = 3000 \text{ A}/\mu\text{s}$	$T_{j} = 125^{\circ}C$		29		μΟ
L			$T_i = 25^{\circ}C$		7		T
E_r	Reverse Recovery Energy		$T_{j} = 125^{\circ}C$		12		mJ
R _{thJC}	Junction to Case Thermal Resistance					0.34	°C/W

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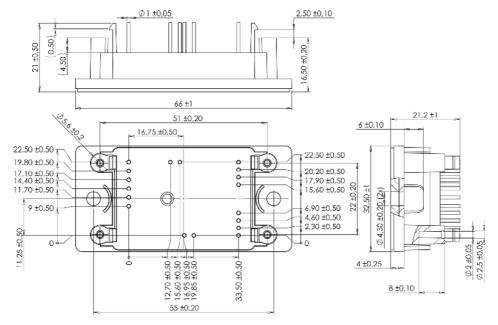


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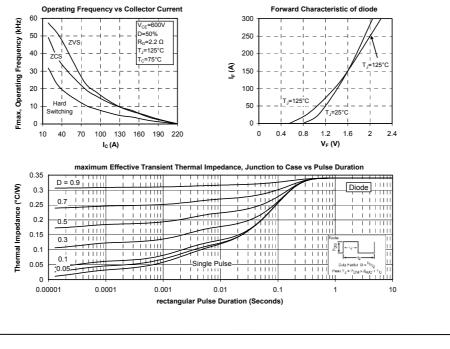
Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T _J	Operating junction temperature range		-40		150		
T _{STG}	Storage Temperature Range			-40		125	°C
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					75	g

SP2 Package outline (dimensions in mm)



Typical Performance Curve

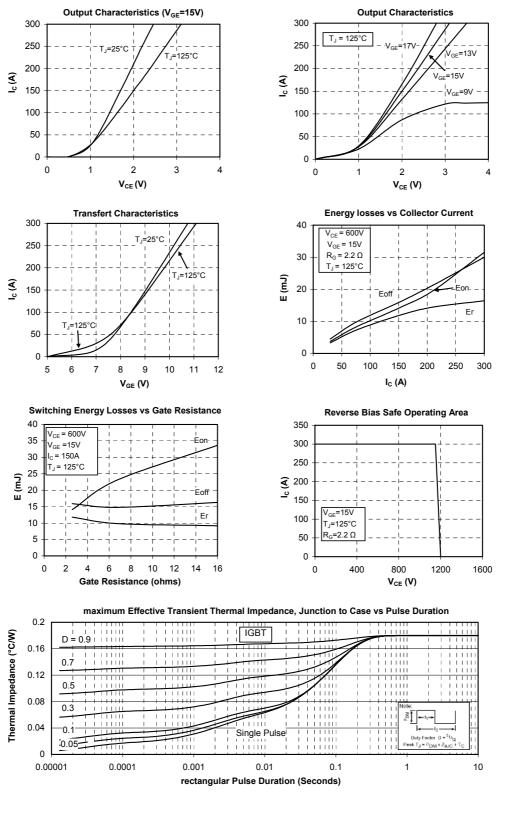


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